

TSD840MD

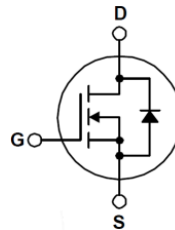
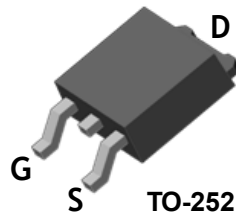
500V N-Channel MOSFET

General Description

This Power MOSFET is produced using Truesemi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 8.0A,500V,Max. $R_{DS(on)}=0.95\ \Omega$ @ $V_{GS}=10V$
- 100% avalanche tested
- High ruggedness
- Fast switching
- Improved dv/dt capability



Absolute Maximum Ratings $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current	$T_C = 25^\circ\text{C}$	8.0*
		$T_C = 100^\circ\text{C}$	5.0*
I_{DM}	Pulsed Drain Current (Note 1)	32	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	280	mJ
E_{AR}	Repetitive Avalanche Energy (Note 1)	6.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) -Derate above 25°C	100	W
		0.36	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Resistance Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.9	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics $T_J=25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$	--	0.88	0.95	Ω

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to $25\text{ }^\circ\text{C}$	--	--	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 400\text{ V}, T_J = 125\text{ }^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1400	--	pF
C_{oss}	Output Capacitance		--	210	--	pF
C_{riss}	Reverse Transfer Capacitance		--	80	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Time	$V_{DS} = 250\text{ V}, I_D = 8.0\text{ A}, R_G = 25\text{ }\Omega$ (Note 4,5)	--	15	--	ns
t_r	Turn-On Rise Time		--	62	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	93	--	ns
t_f	Turn-Off Fall Time		--	48	--	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 8.0\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4,5)	--	26	--	nC
Q_{gs}	Gate-Source Charge		--	4	--	nC
Q_{gd}	Gate-Drain Charge		--	13	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

I_S	Continuous Source-Drain Diode Forward Current	--	--	8.0	A	
I_{SM}	Pulsed Source-Drain Diode Forward Current	--	--	24.0		
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 3.0\text{ A}, V_{GS} = 0\text{ V}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$I_S = 8.0\text{ A}, V_{GS} = 0\text{ V}$	--	340	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	3	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=5\text{ mH}, I_{AS}=10.6\text{ A}, V_{DD}=50\text{ V}, V_G=10\text{ V}$, Starting $T_J=25\text{ }^\circ\text{C}$
3. $I_{SD} \leq 8.0\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25\text{ }^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

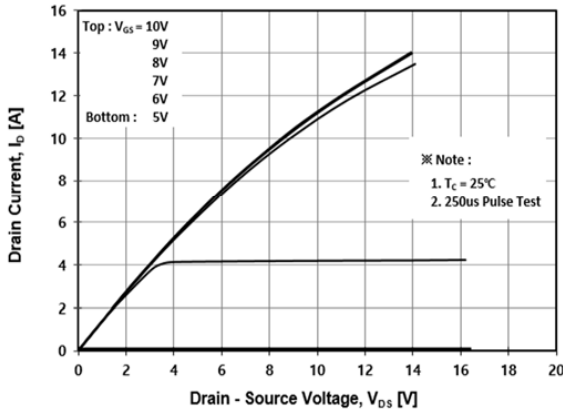


Fig. 2 Typical Output Characteristics

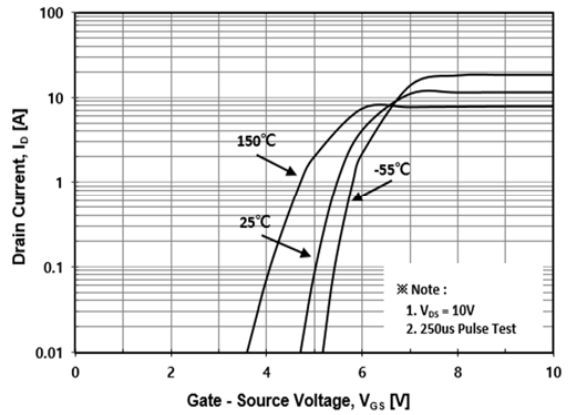


Fig.3 On-Resistance Variation with Drain Current and Gate

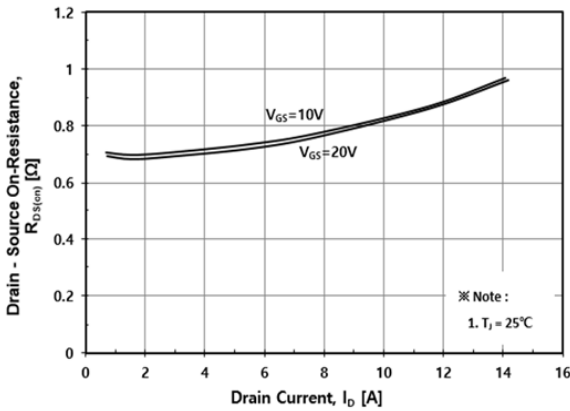


Fig. 4 Body Diode Forward Voltage Variation with Source Current and

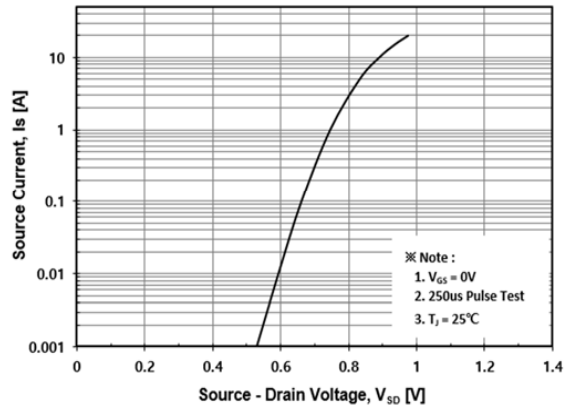


Fig. 5 Typical Capacitance Characteristics

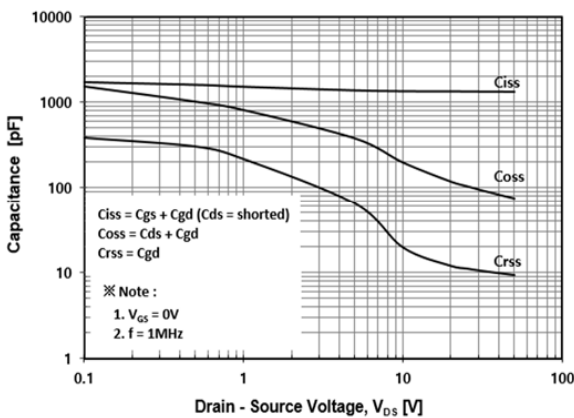


Fig. 6 Typical Total Gate Charge Characteristics

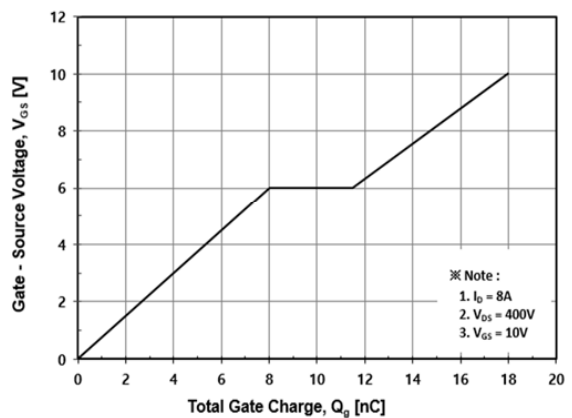


Fig. 7 Breakdown Voltage Variation vs. Temperature

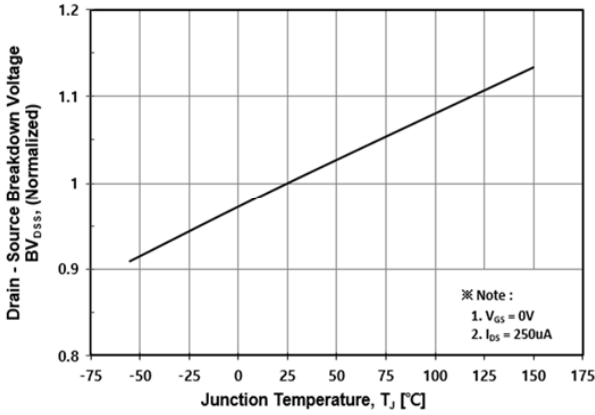


Fig. 8 On-Resistance Variation vs. Temperature

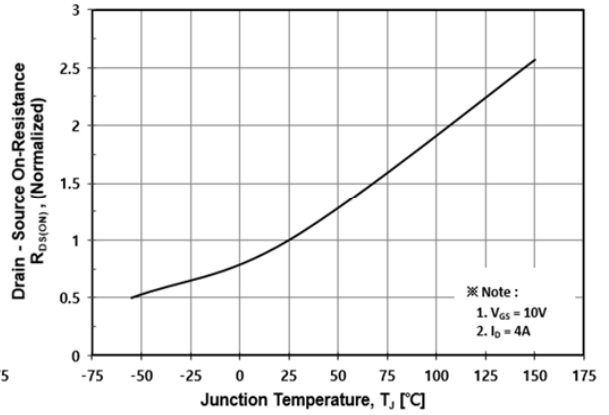


Fig. 9 Maximum Drain Current vs. Case Temperature

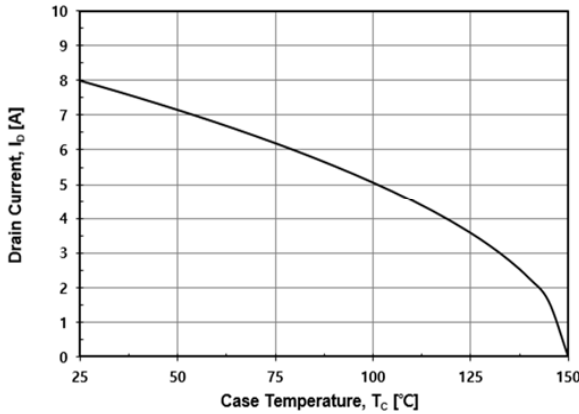


Fig. 10 Maximum Safe Operating Area

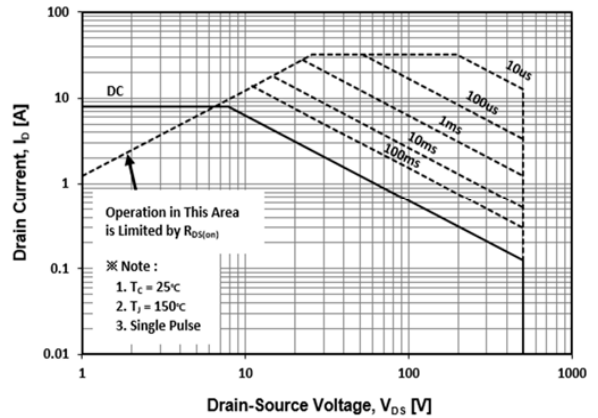


Fig. 11 Transient Thermal Impedance

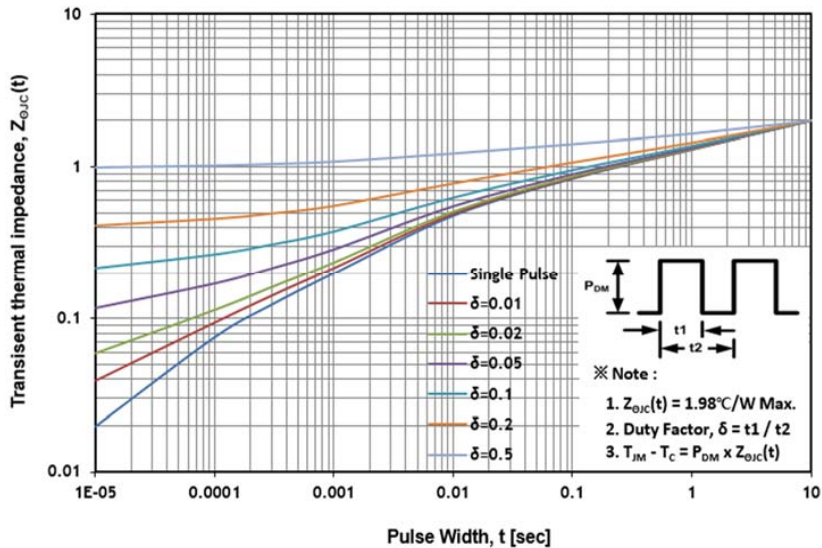


Fig. 12 Gate Charge Test Circuit & Waveform

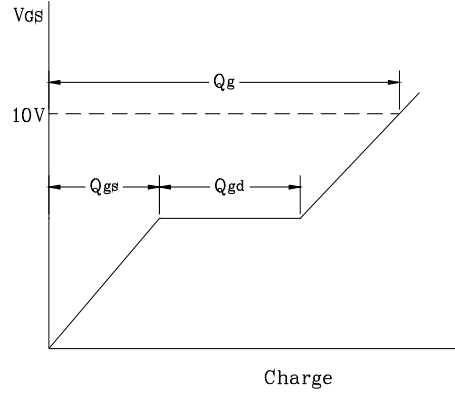
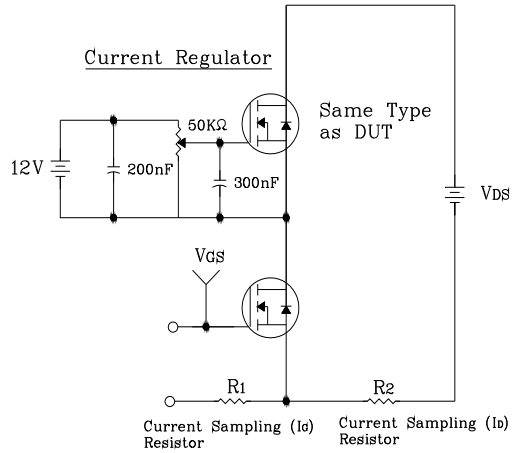


Fig. 13 Resistive Switching Test Circuit & Waveform

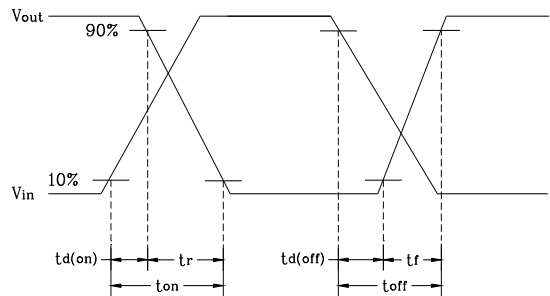
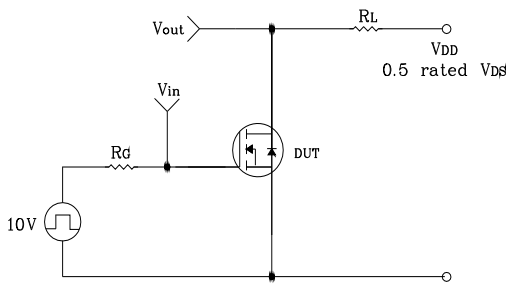


Fig. 14 EAS Test Circuit & Waveform

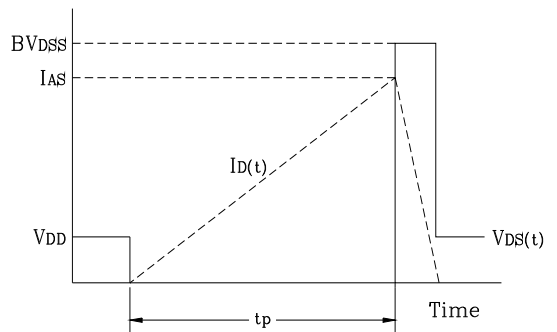
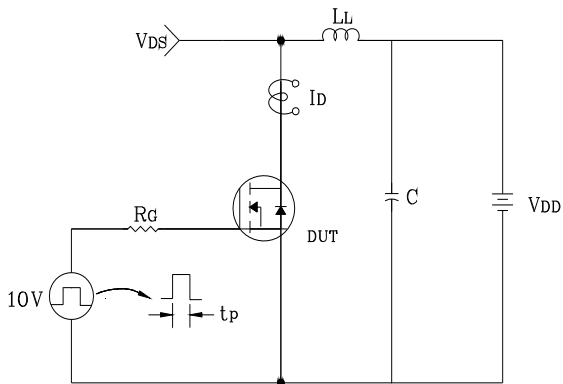


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform

